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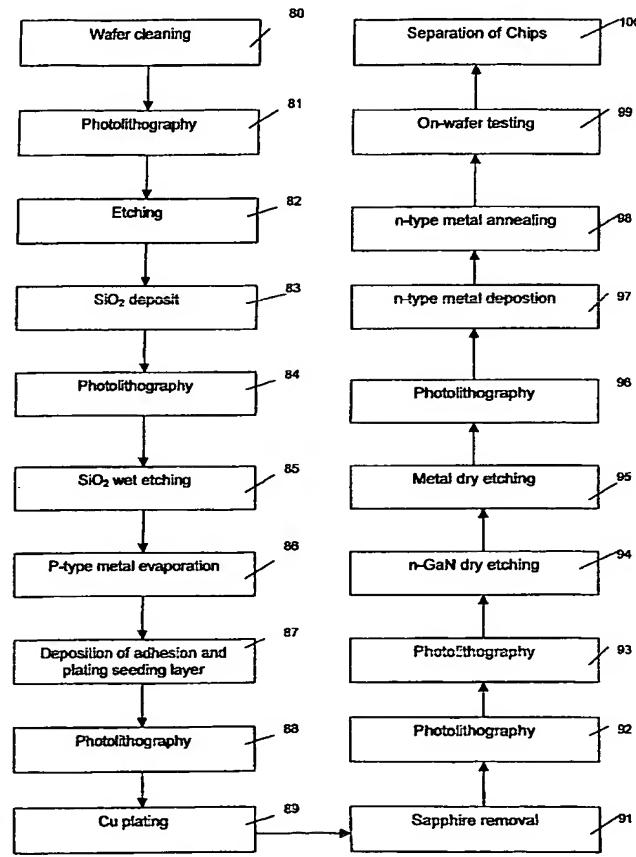
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(54) Title: FABRICATION OF CONDUCTIVE METAL LAYER ON SEMICONDUCTOR DEVICES



(57) Abstract: A method for fabrication of a light emitting device on a substrate, the light emitting device having a wafer with multiple epitaxial layers and an ohmic contact layer on the epitaxial layers remote from the substrate. The method includes the steps:(a) applying to the ohmic contact layer a seed layer of a thermally conductive metal;(b) electroplating a relatively thick layer of the conductive metal on the seed layer; and(c) removing the substrate.A corresponding light emitting device is also disclosed. The light emitting device is a GaN light emitting diode or laser diode.

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